

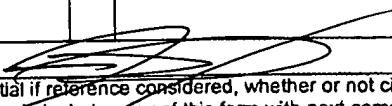
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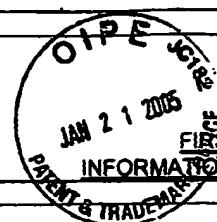
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				ATTY. DOCKET NO. 1875.0220001	APPLICATION NO. To Be Assigned		
				FIRST NAMED INVENTOR Vincent Chen	FILING DATE Herewith	ART UNIT To Be Assigned	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
<i>W</i>	AA1	4,173,791	11/1979	Bell, Antony G.	<i> </i>	<i> </i>	
<i>W</i>	AB1	4,499,557	02/1985	Holmberg et al.	<i> </i>	<i> </i>	
<i>W</i>	AC1	5,163,180	11/1992	Eltoukhy et al.	<i> </i>	<i> </i>	
<i>W</i>	AD1	5,480,828	01/1996	Hsu et al.	<i> </i>	<i> </i>	
<i>W</i>	AE1	5,742,555	04/1998	Marr et al.	<i> </i>	<i> </i>	
<i>W</i>	AF1	5,748,025	05/1998	Ng et al.	<i> </i>	<i> </i>	
<i>W</i>	AG1	5,834,824	11/1998	Shepherd et al.	<i> </i>	<i> </i>	
<i>W</i>	AH1	5,886,392	03/1999	Schuegraf	<i> </i>	<i> </i>	
<i>W</i>	AI1	5,949,712	09/1999	Rao et al.	<i> </i>	<i> </i>	
<i>W</i>	AJ1	6,044,012	03/2000	Rao et al.	<i> </i>	<i> </i>	
<i>W</i>	AK1	6,096,580	08/2000	Iyer et al.	<i> </i>	<i> </i>	
FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AL1						Yes
	AM1						No
	AN1						Yes
	AO1						No
	AP1						Yes
							No
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>W</i>	AR	1	Clark, Lawrence T., "A High-Voltage Output Buffer Fabricated on a 2V CMOS Technology," <i>Symposium on VLSI Circuits Digest of Technical Papers</i> , pp. 61-62, 1999.				
<i>W</i>	AS	1	International Search Report for PCT/US01/48853, 5 pages, July 31, 2002.				
<i>W</i>	AT	1	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. E6.5(a), Oxide failure modes, John Wiley & Sons, Inc., 2 nd Edition, p. 391, 1998.				
EXAMINER <i> </i>				DATE CONSIDERED <i>2/5/05</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

5/20/04

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			FIRST NAMED INVENTOR Vincent Chen				
			FILING DATE Herewith		ART UNIT To Be Assigned		
			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE	
2	AA2 6,096,610	08/2000	Alavi et al.				
2	AB2 6,184,726 B1	02/2001	Haeblerli et al.			06/29/1999	
2	AC2 6,266,269 B1	07/2001	Karp et al.			06/07/2000	
2	AD2 6,351,425 B1	02/2002	Porter, Stephen R.			12/07/2000	
2	AE2 6,477,094 B2	11/2002	Kim et al.			12/18/2000	
2	AF2 6,549,458 B1	04/2003	Rao et al.			10/25/2001	
2	AG2						
2	AH2						
2	AI2						
2	AJ2						
2	AK2						
FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
2	AL2					Yes No	
2	AM2					Yes No	
2	AN2					Yes No	
2	AO2					Yes No	
2	AP2					Yes No	
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
2	AR 2	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. 6.40, Charge-to-breakdown as a function of oxide thickness, John Wiley & Sons, Inc., 2 nd Edition, p. 397, 1998.					
2	AS 2	Shi, Y., et al., "Polarity-Dependent Tunneling Current and Oxide Breakdown in Dual-Gate CMOSFET's," IEEE Electron Device Letters, Volume 19, No. 10, pp. 391-393, October 1998.					
2	AT 2						
EXAMINER 				DATE CONSIDERED 			
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FORM PTO-1449

FIRST SUPPLEMENTAL
INFORMATION DISCLOSURE STATEMENT

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ATTY. DOCKET NO.

1875.0220001

APPLICATION NO.

10/849,295

FIRST NAMED INVENTOR

Vincent CHEN

FILING DATE

May 20, 2004

ART UNIT

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
P	AG2	6,445,619 B1	09/2002	Mihnea et al.		08/01/2001
P	AH2	6,566,189 B2	05/2003	Joo et al.		07/02/2001

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
						Yes
						No
						Yes
						No
						Yes
						No
						Yes
						No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER

DATE CONSIDERED

2/9/05

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